In the Claims:

Please amend the claims as follows:

1-11. (Cancelled).

12. (Previously presented) A method of making an apparatus comprising a substrate and a dielectric layer, comprising the steps of:

providing a substrate;

providing a dielectric layer comprising a first dielectric material on said substrate, said dielectric layer having a dielectric layer thickness and being traversed by through holes passing from an interface with said substrate, to an opposite side of said dielectric layer; providing a reaction initiator on said substrate prior to providing said dielectric layer on said substrate, wherein the providing of said dielectric layer does not deactivate a portion of said reaction initiator located near entrances of said through holes; and

providing a second dielectric material that reacts with said reaction initiator and which at least partially blocks said through holes.

13. (Cancelled).

14. (Cancelled).

15. (Previously presented) A method of making an apparatus comprising a substrate and a dielectric layer, comprising the steps of:

providing a substrate;

providing a dielectric layer comprising a first dielectric material on said substrate, said dielectric layer having a dielectric layer thickness and being traversed by through holes passing from an interface with said substrate, to an opposite side of said dielectric layer;

providing a reaction initiator on said opposite side of said dielectric layer;

coating a reaction initiator deactivator on said reaction initiator except at regions overlying through holes; and

providing a second dielectric material that reacts with said reaction initiator at such regions and which then at least partially blocks said through holes.

16. (Currently amended) A method of making an apparatus comprising a substrate and a dielectric layer, comprising the steps of:

providing a substrate;

providing a dielectric layer comprising a first dielectric material on said substrate, said dielectric layer having a dielectric layer thickness and being traversed by through holes passing from an interface with said substrate, to an opposite side of said dielectric layer; and

providing a second dielectric material ~~that at least partially blocks said through holes; said second dielectric material being applied to~~ on said opposite side of said dielectric layer; and

applying ~~while~~ an electric field ~~is applied~~ to said substrate to cause said second dielectric material to at least partially block said through holes.

17. (Previously presented) The method of claim 12, further comprising the step of forming a semiconductor layer on said dielectric layer.

18. (Previously presented) The method of claim 15, in which said dielectric layer comprises pits and bumps that produce surface roughness in one surface of said dielectric layer, wherein said deactivator leaves said reaction initiator uncoated at pits and bumps, and wherein said second dielectric material at least partially fills said pits and at least partially smoothes areas surrounding said bumps in a manner that reduces said roughness.

19. (Previously presented) The method of claim 12, in which said providing a dielectric layer produces a layer thickness within a range of between about 10 nanometers and about 5 microns.

20. (Previously presented) The method of claim 17, further comprising the step of forming a source electrode and a drain electrode in a spaced apart arrangement on said semiconductor layer.

21. (Previously presented) The method of claim 12, further comprising the step of forming a conductor on said dielectric layer.

22. (Currently amended) The method of claim 12, in which the ~~comprising the step of providing~~ through holes have ~~having~~ average diameters substantially smaller than an average spacing between mutually adjacent ~~said~~ through holes.

23. (Previously presented) The method of claim 15, in which said step of coating said deactivator comprises the step of transferring said deactivator from a flat stamping surface onto said reaction initiator.

24. (Previously presented) The method of claim 15, further comprising the step of forming a semiconductor layer on said dielectric layer.

25. (Previously presented) The method of claim 15, in which said dielectric layer comprises pits and bumps that produce surface roughness in one surface of said dielectric layer, and wherein said second dielectric material at least partially fills said pits and at least partially smoothes areas surrounding said bumps in a manner that reduces said roughness.

26. (Previously presented) The method of claim 15, in which said providing a dielectric layer produces a layer thickness within a range of between about 10 nanometers and about 5 microns.

27. (Previously presented) The method of claim 24, further comprising the step of forming a source electrode and a drain electrode in a spaced apart arrangement on said semiconductor layer.

28. (Previously presented) The method of claim 15, further comprising the step of forming a conductor on said dielectric layer.

29. (Previously presented) The method of claim 16, further comprising the step of forming a semiconductor layer on said dielectric layer.

30. (Previously presented) The method of claim 16, in which said providing a dielectric layer produces a layer thickness within a range of between about 10 nanometers and about 5 microns.

31. (Previously presented) The method of claim 29, further comprising the step of forming a source electrode and a drain electrode in a spaced apart arrangement on said semiconductor layer.

32. (Previously presented) The method of claim 16, further comprising the step of forming a conductor on said dielectric layer.

33. (Currently amended) The method of claim 16, in which the ~~comprising the step of providing~~ through holes have ~~having~~ average diameters substantially smaller than an average spacing between mutually adjacent ~~said~~ through holes.

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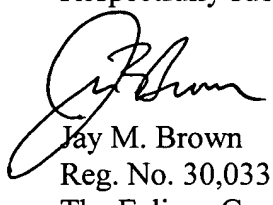
Respectfully submitted,



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